

1 ABSTRACT OF THE DISCLOSURE

2 Oxide/Nitride Stacked FinFET Spacer Process

3 In a FinFET integrated circuit, the fins are formed with a body thickness in  
4 the body area and then thickened in the source/drain area outside the body  
5 to improve conductivity. The thickening is performed with epitaxial  
6 deposition while the gates are covered by a composite gate cover layer to  
7 prevent thickening of the gates, which may short the gate to the  
8 source/drain.